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(71) Applicant (for all designated States except US): **KONINKLIJKE PHILIPS ELECTRONICS N.V.** [NL/NL];  
Groenewoudseweg 1, NL-5621 BA Eindhoven (NL).

(71) Applicant (for DE, GB, JP only): **INTERUNIVERSITAIR MICROELEKTRONICA CENTRM VZW**  
[BE/BE]; Kapeldreef 75, B-3001 Leuven (BE).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **MEUNIER-BEILLARD, Philippe** [FR/BE]; c/o Prof. Holstlaan 6, NL-5656

AA Eindhoven (NL). **CAYMAX, Mathieu, R., J.**  
[BE/BE]; c/o Kapeldreef 75, B-3001 Leuven (NL).

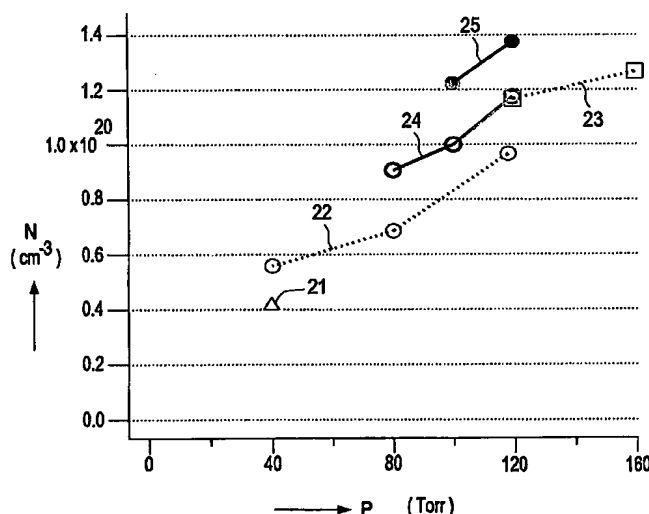
(74) Agent: **DUIJVESTIJN, Adrianus, J.**; Prof. Holstlaan 6,  
NL-5656 AA Eindhoven (NL).

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[Continued on next page]

(54) Title: METHOD OF EPITAXIAL DEPOSITION OF AN N-DOPED SILICON LAYER



(57) Abstract: The invention relates to a method of manufacturing a semiconductor device (10) with a semiconductor body (1) comprising silicon is provided with an n-type doped semiconductor region (2) comprising silicon by means of an epitaxial deposition process, wherein the epitaxial deposition process of the n-type region is performed by positioning the semiconductor body (1) in an epitaxial reactor and introducing in the reactor a first gas stream comprising a carrier gas and further gas streams comprising a gaseous compound comprising silicon and a gaseous compound comprising an element from the fifth column of the periodic system of elements, while heating the semiconductor body (1) to a growth temperature (T<sub>g</sub>) and using an inert gas as the carrier gas. According to the invention for the gaseous compound comprising silicon a mixture is chosen of a first gaseous silicon compound which is free of chlorine and a second gaseous silicon compound comprising chlorine. Such a method allows for a very high carrier concentration in the in-situ doped grown region (3). Nitrogen is the preferred carrier gas.

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